

2STF1340

Low voltage fast-switching NPN power transistor

Features

- Very low collector-emitter saturation voltage
- High current gain characteristic
- Fast switching speed

Applications

- LED
- Motherboard & hard disk drive
- Mobile equipment
- DC-DC converter

Description

The 2STF1340 is a NPN transistor manufactured using new "PB-HCD" (power bipolar high current density) technology. The resulting transistor shows exceptional high gain performances coupled with very low saturation voltage.

The complementary PNP is the 2STF2340.

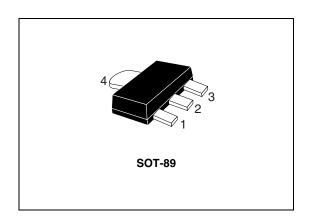


Figure 1. Internal schematic diagram

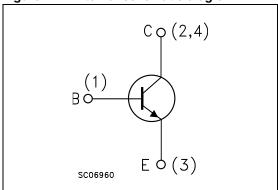


Table 1. Device summary

Order code	Marking	Package	Packaging
2STF1340	1340	SOT-89	Tape and reel

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Electrical ratings 2STF1340

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{BE} = 0)	40	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	40	V
V _{EBO}	Emitter-base voltage (I _C = 0)	5	V
I _C	Collector current	3	Α
I _{CM}	Collector peak current (t _P < 5 ms)	6	Α
P _{tot}	Total dissipation at T _{amb} = 25 °C	1.4	W
T _{stg}	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thJA} ⁽¹⁾	Thermal resistance junction-ambient max	89	°C/W

^{1.} Device mounted on PCB area of 1 cm²



2 Electrical characteristics

 T_{case} = 25 °C unless otherwise specified.

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E = 0)	V _{CB} = 40 V			0.1	μΑ
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 5 V			0.1	μΑ
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = 100 μA	40			V
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage (I _B = 0)	I _C = 10 mA	40			>
V _{(BR)EBO}	Emitter-base breakdown voltage $(I_C = 0)$	I _E = 100 μA	5			V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	$I_C = 2 A$ $I_B = 100 mA$ $I_C = 3 A$ $I_B = 150 mA$			250 350	mV mV
V _{BE(sat)} (1)	Base-emitter saturation voltage	I _C = 2 A I _B = 100 mA			1.2	V
h _{FE} ⁽¹⁾	DC current gain	$\begin{split} I_{C} &= 0.1 \text{ A} & V_{CE} = 2 \text{ V} \\ I_{C} &= 1 \text{ A} & V_{CE} = 2 \text{ V} \\ I_{C} &= 3 \text{ A} & V_{CE} = 2 \text{ V} \end{split}$	100 180	220	450	
f _T	Transition frequency	$I_C = 0.1 \text{ A}$ $V_{CE} = 5 \text{ V}$ $f = 100 \text{ MHz}$	100			MHz
C _{CBO}	Collector-base capacitance (I _E = 0)	f = 1 MHz V _{CB} = 10 V		30		pF
t _{on} t _{off}	Resistive load Turn-on time Turn-off time	$\begin{split} I_{C} &= 1.5 \text{ A} & V_{CC} = 10 \text{ V} \\ I_{B(on)} &= -I_{B(off)} = 150 \text{ mA} \\ V_{BB(off)} &= -5 \text{ V} \end{split}$		65 750		ns ns

^{1.} Pulse test: pulse duration \leq 300 μ s, duty cycle \leq 2 %

Electrical characteristics 2STF1340

2.1 Electrical characteristics (curves)

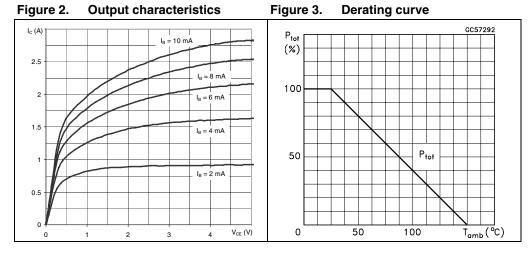


Figure 4. DC current gain ($V_{CE} = 2 \text{ V}$) Figure 5. DC current gain ($V_{CE} = 5 \text{ V}$)

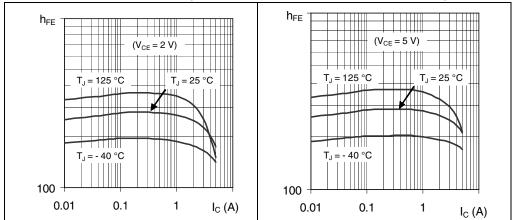
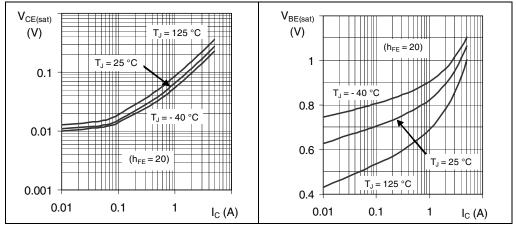
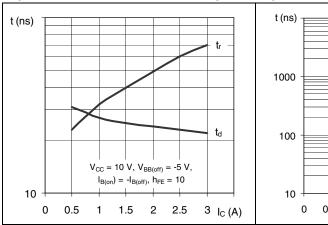


Figure 6. Collector-emitter saturation Figure 7. Base-emitter saturation voltage voltage



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Figure 8. Resistive load switching on Figure 9. Resistive load switching off



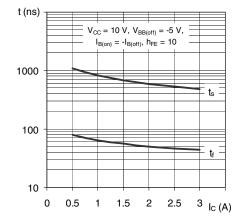
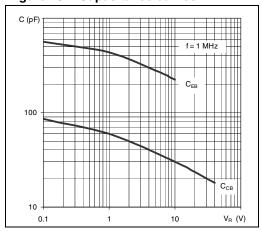
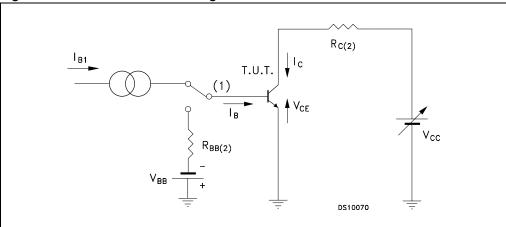


Figure 10. Capacitance curves



2.2 Test circuits

Figure 11. Resistive load switching



- 1. Fast electronic switch
- 2. Non-inductive resistor

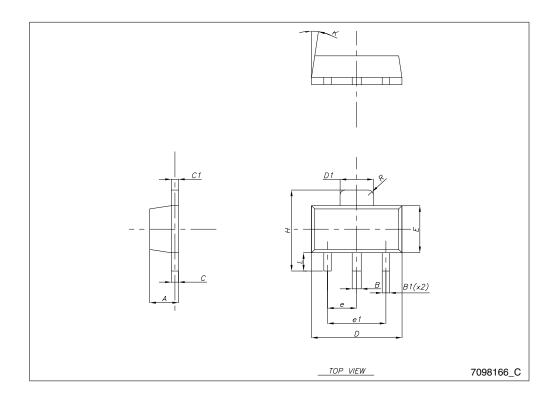
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of $\mathsf{ECOPACK}^{\mathbb{B}}$ packages, depending on their level of environmental compliance. $\mathsf{ECOPACK}^{\mathbb{B}}$ specifications, grade definitions and product status are available at: $\mathit{www.st.com}$. $\mathsf{ECOPACK}^{\mathbb{B}}$ is an ST trademark.

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SOT-89 mechanical data

Dim.	mm			
	Min.	Тур.	Max.	
A	1.40		1.60	
В	0.44		0.56	
B1	0.36		0.48	
С	0.35		0.44	
C1	0.35		0.44	
D	4.40		4.60	
D1	1.62		1.83	
E	2.29		2.60	
е	1.42		1.57	
e1	2.92		3.07	
Н	3.94		4.25	
К	1°		8°	
L	0.89		1.20	
R		0.25		



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2STF1340 Revision history

4 Revision history

Table 5. Document revision history

Date	Revision	Changes
20-Oct-2006	1	Initial release
19-Oct-2009	2	Document status promoted from preliminary data to datasheet, inserted electrical characteristics (curves) section and updated mechanical data

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